

Description

The HD6956 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



TO252-2L

General Features

V_{DS} = 60V I_D =50 A

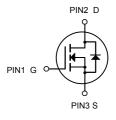
 $R_{DS(ON)}$ < 15m Ω @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HD6956	TO252-2L	HD6956 XXYYS	2500

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter Ratin		ng Units		
Vos	Drain-Source Voltage	60	V		
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20			
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ 50			
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ 25			
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ 7.4			
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ¹	Continuous Drain Current, V _{GS} @ 10V ¹ 6			
Ірм	Pulsed Drain Current ²		А		
EAS	Single Pulse Avalanche Energy ³	Single Pulse Avalanche Energy ³ 39.2			
las	Avalanche Current	lanche Current 28			
P _D @T _C =25°C	Total Power Dissipation ⁴	Total Power Dissipation ⁴ 45			
P _D @T _A =25°C	Total Power Dissipation ⁴ 2		W		
Тѕтс	Storage Temperature Range -55 to 150		°C		
TJ	Operating Junction Temperature Range	erating Junction Temperature Range -55 to 150 °C			
R _θ JA	Thermal Resistance Junction-Ambient ¹	62 °C/W			



R _θ JC	Thermal Resistance Junction-Case ¹	2.8	°C/W
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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
△BV _{DSS} /△T _J	^r _{DSS} /△TJ BV _{DSS} Temperature Coefficient Reference to 25°C , I _D =1mA			0.057		V/°C
		V _{GS} =10V , I _D =20A		11	15	
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =10A		15	20	$\mathbf{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage		1.2		2.5	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA		-5.68		mV/°C
		V _{DS} =48V , V _{GS} =0V , T _J =25°C			1	
loss	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =55°C			5	uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =15A		45		S
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω
Qg	Total Gate Charge (4.5V)			19.3		
Qgs	Gate-Source Charge	V _{DS} =48V , V _{GS} =4.5V , I _D =15A		7.1		nC
Q _{gd}	Gate-Drain Charge			7.6		
T _{d(on)}	Turn-On Delay Time			7.2		
Tr	Rise Time	V _{DD} =30V , V _{GS} =10V ,		50		
Td(off)	Turn-Off Delay Time	R _G =3.3 , I _D =15A		36.4		ns
T _f	Fall Time			7.6		
C _{iss}	Input Capacitance			2423		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		145		pF
Crss	Reverse Transfer Capacitance			97		
ls	Continuous Source Current ^{1,5}				35	Α
Іѕм	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current			80	Α
VsD	Diode Forward Voltage ²	V _{GS} =0V , I _S =A , T _J =25°C			1	V
t _{rr}	Reverse Recovery Time	I- 45A		16.3		nS
Q _{rr}	Reverse Recovery Charge	IF=15A , dI/dt=100A/μs , T _J =25°C		11		nC

Note:

- 1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leqq 300us , duty cycle \leqq 2%
- 3.The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=28A
- 4. The power dissipation is limited by 150° C junction temperature 5. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation



Typical Characteristics

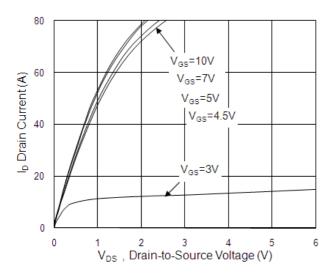


Fig.1 Typical Output Characteristics

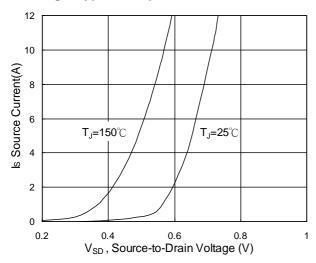


Fig.3 Forward Characteristics of Reverse

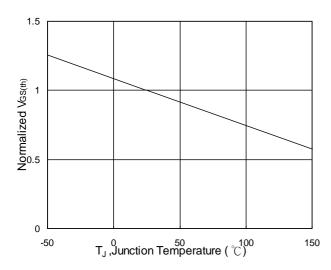


Fig.5 Normalized V_{GS(th)} v.s T_J

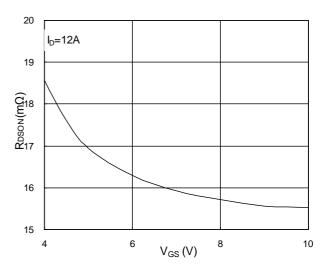


Fig.2 On-Resistance v.s Gate-Source

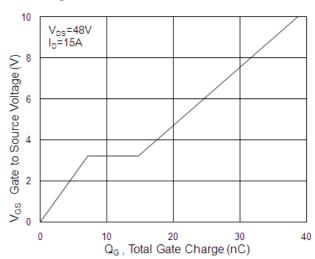


Fig.4 Gate-Charge Characteristics

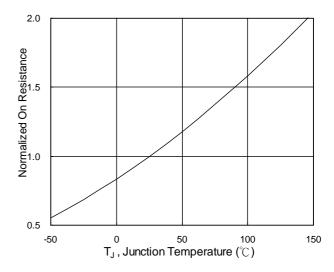


Fig.6 Normalized R_{DSON} v.s T_J

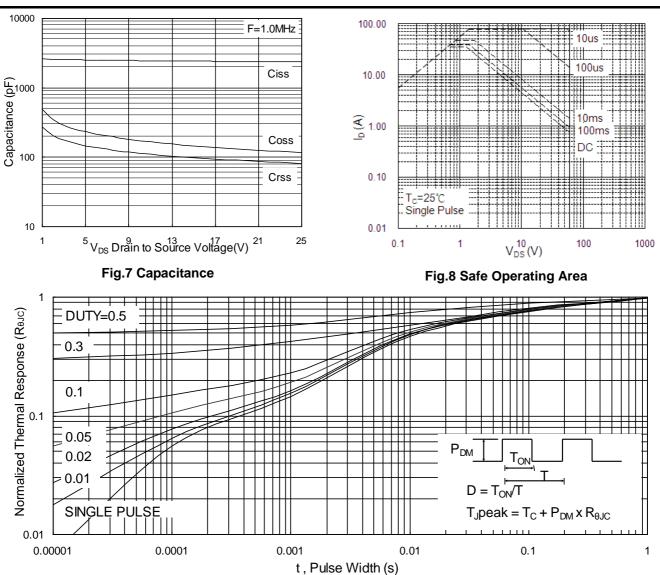


Fig.9 Normalized Maximum Transient Thermal Impedance

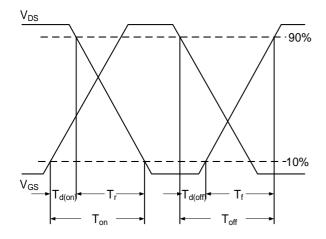


Fig.10 Switching Time Waveform

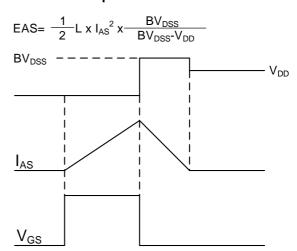
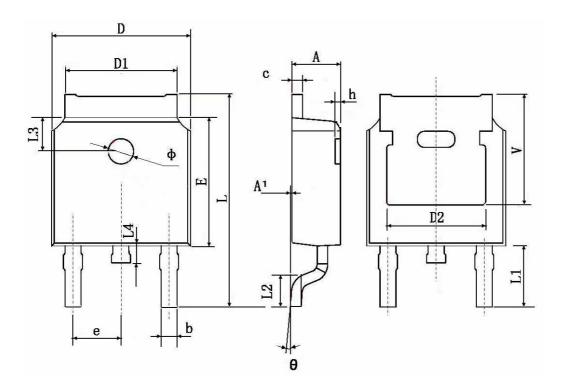


Fig.11 Unclamped Inductive Switching Waveform



TO252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483 TYP.		0.190	TYP.	
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		



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